Photoluminescence and Raman spectroscopy characterization of boron- and nitrogen-doped 6H silicon carbide

Boron- and nitrogen-doped 6H silicon carbide epilayers grown on low off-axis 6H silicon carbide substrates have been characterized by photoluminescence and Raman spectroscopy. Combined with secondary ion mass spectrometry results, preferable doping type and optimized concentration could be proposed to obtain strong donor to acceptor pair band luminescence.

General information
Publication status: Published
Organisations: Nanophotonic Devices, Department of Photonics Engineering, Energy and Materials, Department of Chemistry, Linköping University, KTH - Royal Institute of Technology, Meijo University, Technical University of Denmark
Pages: We P-58
Publication date: 2011

Host publication information
Title of host publication: Proceedings of ICSCRM
Keywords: Raman spectroscopy, 6H-SiC, Photoluminescence, Sublimation epitaxy
URLs:
https://icscrm2011.org/
Source: orbit
Source-ID: 278619
Research output: Chapter in Book/Report/Conference proceeding › Article in proceedings – Annual report year: 2011 › Research › peer-review